

# Empirical Evaluation of NAND Flash Memory Performance

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## ABSTRACT

Reports of NAND flash device testing in the literature have for the most part been limited to examination of circuit-level parameters on raw flash chips or prototypes, and system-level parameters on entire storage subsystems. However, there has been little examination of system-level parameters of raw devices, such as mean latency and endurance values.

We report the results of such tests on a variety of devices. Read, program, and erase latency were found to align closely with manufacturer’s specified “typical” values in almost all cases. Program/erase endurance, however, was found to exceed specified minimum values, often by as much as a factor of 100. In addition significant performance changes were found with wear. These changes may be used to track wear, and in addition have significant implications for system performance over the lifespan of a device. Finally, random write patterns which incur performance penalties on current flash-based memory systems were found to incur no overhead on the devices themselves.

## 1. INTRODUCTION

Fixed magnetic disk has been the predominant media for secondary storage for over three decades. In the last five years, however, solid state storage in the form of NAND flash memory has come into increasing use, becoming the first competitor to magnetic disk storage to gain significant commercial acceptance.

With the increasing use of flash-based secondary storage, detailed understanding of behavior which affects operating system design and performance becomes important. However, while disk behavior has been extensively studied, there appear to be few sources for the information needed to predict performance and reliability of flash-based storage systems. Detailed studies of low-level electrical characteristics are available [5, 6, 10], as well as performance studies of complete storage assemblies (e.g. SSDs) containing flash chips and controllers [1, 9]. However, to the best of our knowledge, there is no experimental study to date of actual

flash chips giving measured values for read, write, and erase speed, power consumption, or write/erase longevity.

This paper reports measurements of these parameters for a range of raw flash chips. We focus on chips themselves, rather than flash-based systems such as USB drives or SSDs, in order to better understand the capabilities and limitations of the underlying technology.

Of the results found, the most unexpected were these:

- High program/erase endurance. Although NAND flash memory degrades with repeated program/erase cycles, measured lifetime varies greatly, and is often as much as 100× higher than manufacturer specifications.
- Wear-dependent performance changes. On all chips tested, repeated program/erase cycling of a single block decreases write time and increases erase time—by as much as a factor of three or more—as that block wears out. This changes overall system performance, as well as providing a predictor of individual block failure.
- Random program speed. Flash-based storage systems such as SSDs often have poor random write performance [1], but this is not an attribute of the technology itself. In our testing, non-sequential writes were found to perform as well as sequential ones.

In the remainder of this paper we first present an overview of flash memory technology from a system perspective in Section 2, followed by experimental results (Section 3) and conclusions (Section 4).

## 2. BACKGROUND

NAND flash is a form of electrically erasable programmable read-only memory based on a particularly space-efficient basic cell, optimized for mass storage applications. Unlike most memory technologies, NAND flash is organized in *pages* of typically 2K or 4K bytes which are read and written as a unit. Unlike block-oriented disk drives, however, pages must be erased in units of *erase blocks* comprising multiple pages—typically 32 to 128—before being re-written.

### 2.1 Technical Overview

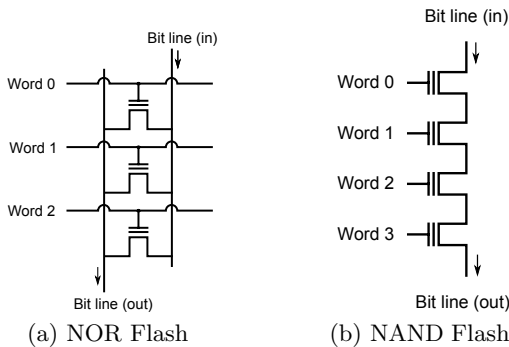
To inform our discussion we present an overview of the circuit and electrical aspects of flash technology which are relevant to system software performance; a deeper discussion of these and other issues may be found in the survey by Sanvido *et al* [11].

**Cell architecture:** The basic cell in a NAND flash is a MOSFET transistor with a floating (i.e. oxide-isolated)

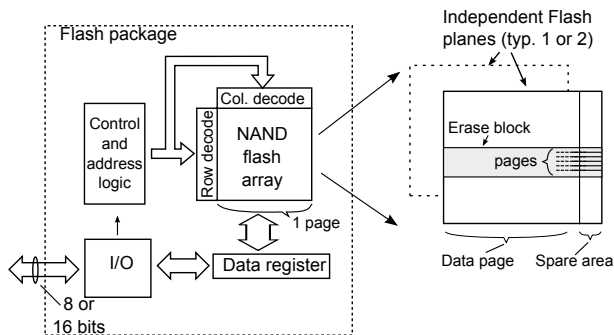
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**Figure 1: Flash circuit structure.** NAND flash is distinguished by the series connection of cells along the bit line, while NOR flash (and other memory technologies) arrange cells in parallel between two bit lines.



**Figure 2: Typical flash chip architecture.** Read and write are both performed in two steps, consisting of the transfer of data over the external bus to or from the data register, and the internal transfer between the data register and the flash array.

gate. Charge is tunneled onto this gate during write operations, and removed (via the same tunneling mechanism) during erasure. This stored charge causes changes in  $V_T$ , the threshold or turn-on voltage of the cell transistor, which may then be sensed by the read circuitry. NAND flash is distinguished from other flash technologies (e.g. NOR flash, E<sup>2</sup>PROM) by the tunneling mechanism (Fowler-Nordheim or FN tunneling) used for both programming and erasure, and the series cell organization shown in Figure 1(b).

Many of the more problematic characteristics of NAND flash are due to this organization, which eliminates much of the decoding overhead found in other memory technologies. In particular, in NAND flash the only way to access an individual cell for either reading or writing is *through* the other cells in its bit line. This adds significant noise to the read process, and also requires care during writing to ensure that adjacent cells in the string are not disturbed. During erasure, in contrast, all cells on the same bit string are erased.

In order to ensure precise programming and erasure in the face of process and temperature variations, an internal state machine repeatedly programs (or erases) a page and reads it back until the operation has succeeded. Earlier generations of NAND flash (and high-performance modern ones) use what is termed Single-Level Cell (SLC) technology, storing a single bit on each cell. High-capacity Multi-Level Cell (MLC) devices use more than two levels on a cell, storing 2 to as many as 4 [13] bits as one of 4 to 16 discrete levels.

**Organization and performance:** With few exceptions

today’s flash chips correspond to the block diagram in Figure 2. Cells are arranged in pages, typically containing 2K or 4K bytes plus a spare area of 64 to 256 bytes for system overhead. Between 16 and 128 pages make up an *erase block*, or *block* for short, which are then grouped into a flash *plane*. Devices may contain independent flash planes, allowing simultaneous operations for higher performance. Finally, a static RAM buffer holds data before writing or after reading, and data is transferred to and from this buffer via an 8- or 16-bit wide bus.

This architecture evolved to meet storage demands for digital photography and MP3 players, with modest performance requirements and strict cost constraints. This is reflected in current flash chips, with low-cost interfaces limited to a peak bandwidth of 40 MB/sec. More recently, the market for high performance SSDs has generated demand for higher transfer rates, resulting in efforts such as ONFI 2.1 [3] to standardize 100 MB/s to 200 MB/s DDR interfaces.

In this study we are interested in the performance of basic operations—i.e. writing from the internal buffer to the flash plane, reading from the flash plane to the buffer, or erasing a block. These represent the fundamental performance limits of any particular NAND flash design, rather than limits of a low-performance I/O interface.

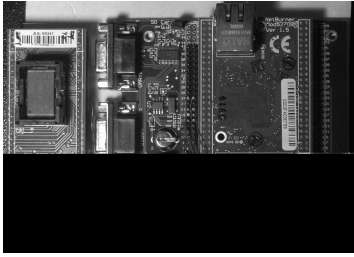
**Reliability:** Unlike other memory technologies, NAND flash is deliberately engineered at densities which result in bit errors in normal operation; error correcting codes (ECC) are then used to avoid corruption of user data. NAND flash errors fall into three categories: program disturbs, read disturbs, and data retention errors.

Program disturbs occur when programming voltage affects non-selected bits on the same bit line, causing a weak programming effect. Although these errors can occur after only a few writes, the resulting error rate is bounded, as the number of writes to an erase block is limited. (typically to one write per page) Read disturbs occur by a similar mechanism, but are caused by the lower voltage levels used in read operations. Although occurring more slowly—perhaps  $10^5$  or  $10^6$  reads to a block are required [8]—the number of reads and thus induced errors is not bounded. Finally, data retention errors occur due to charge leakage over time; they are relatively infrequent, but are exacerbated by temperature and wear.

We do not address reliability in our measurements below; however it has significant implications for storage system design. Recent MLC chips, for instance, require codes which provide 4 bits of correction for every 512 data bytes. In addition, the potential for read disturbs and data retention errors to accumulate over time requires periodic “scrubbing”, where data is read, corrected, and written back.

## 2.2 Related Work

Prior experimental studies of flash memory performance and endurance may be classified as circuit-oriented and system-oriented. Circuit-level studies have examined the effect of program/erase stress on internal electrical characteristics, often using custom-fabricated devices to remove the internal control logic and allow e.g. measurements of the effects of single program or erase steps. A representative study is by Lee et al. at Samsung [6], examining both program/erase cycling and hot storage effects across a range of process technologies. Similar studies include those by Park et al. [10] and Yang et al. [14], both also at Samsung.



**Figure 3: Flash test apparatus.** Test system is based on a NetBurner 5270 controller and TSOP48 programming socket.

| Device         | Size (bits) | Cell | Nominal endurance | Process |
|----------------|-------------|------|-------------------|---------|
| NAND128W3A2BN  | 128M        | SLC  | $10^5$            | 90nm    |
| HY27US08121A   | 512M        | SLC  | $10^5$            | 90nm    |
| MT29F2G08AAD   | 2G          | SLC  | $10^5$            | 50nm    |
| MT29F4G08AAC   | 4G          | SLC  | $10^5$            | 72nm    |
| NAND08GW3B2C   | 8G          | SLC  | $10^5$            | 60nm    |
| MT29F8G08MAAWC | 8G          | MLC  | $10^4$            | 72nm    |
| 29F16G08CANC1  | 16G         | SLC  | $10^5$            | 50nm    |
| MT29F32G08QAA  | 32G         | MLC  | $10^4$            | 50nm    |

**Table 1: Chips tested.** Note that some process technology values are estimated based on manufacturer and production date.

System-level studies have instead examined characteristics of entire flash-based storage systems, such as USB drives and SSDs. The most recent of these presents uFLIP [1], a benchmark for such storage systems, with measurements of a wide range of devices; this work quantifies the degraded performance observed for random writes in many such devices. Additional work in this area includes [2] and [9]. There has been a small amount of empirical testing of raw flash chips in the wireless sensor network community [7], but this work has focused primarily on energy usage and has not addressed performance or endurance.

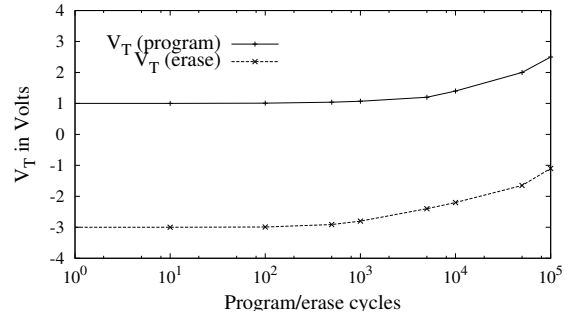
### 3. EXPERIMENTAL RESULTS

#### 3.1 Methodology

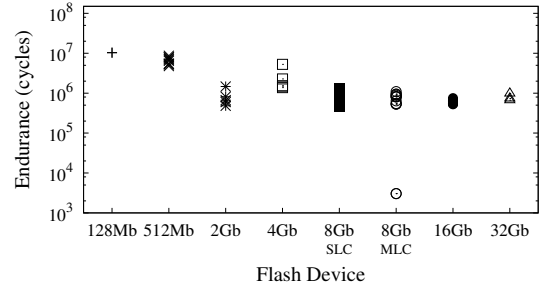
In order to test a wide range of chips, flash devices were acquired both through traditional distributors and by purchasing and disassembling mass-market storage devices. A programmable flash controller was constructed using software control of general-purpose I/O pins on a micro-controller to implement the flash interface protocol for 8-bit devices; this test setup may be seen in Figure 3. Chips tested ranged from early 128 Mbit (16 MB) SLC devices to recent 16 Gbit and 32 Gbit MLC chips. A complete list of devices tested may be seen in Table 1. In most cases a single sample of a chip was used; however multiple instances of the 16 Gbit and 512 Mbit chips were tested. Unless otherwise specified, all tests were performed at 25° C.

#### 3.2 Endurance

Limited write endurance is a key characteristic of flash memory, and all floating gate devices in general, which is not present in competing memory and storage technologies. As blocks are repeatedly erased and programmed, the oxide layer isolating the gate degrades, as described in more detail in [5]. This in turn causes a change in the response of the cell to a fixed programming or erase step, as shown in



**Figure 4: Typical  $V_T$  degradation with program/erase cycling.** Data is abstracted from [6], [10], and [14].



**Figure 5: Program/Erasure endurance by device.** Measured lifetimes of individual blocks are plotted. Nominal endurance for devices tested is  $10^5$  cycles for all devices except the 8 Gbit MLC and 32 Gbit device, which are rated for  $10^4$  cycles.

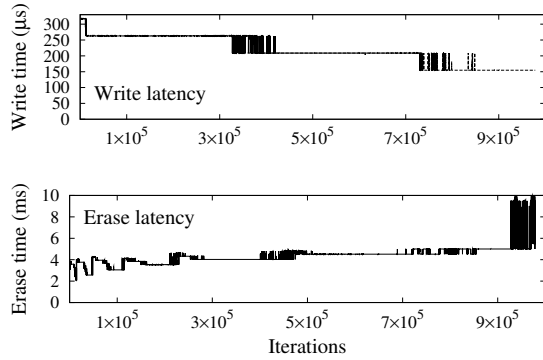
Figure 4. In practice this degradation is compensated for by adaptive programming and erase algorithms internal to the chip, which use multiple program/read or erase/read steps to achieve the desired state. If a cell has degraded too much, however, the program or erase operation will terminate in an error, after which the external system must consider the block *bad* and remove it from use.

Program/erase endurance was tested by repeatedly programming a single page with all zeroes (the programmed state for SLC flash), and then erasing the containing block. Although rated device endurance ranges from  $10^4$  to  $10^5$  program/erase cycles, in Figure 5 we see that measured endurance was higher, often by nearly two orders of magnitude, with a small number of outliers.

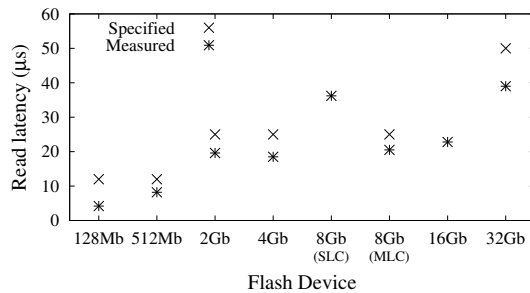
Timing traces were collected during endurance tests, and a representative trace is shown in Figure 6. Cell degradation of  $V_T$  appears to be affecting the iterative programming and erase algorithms here: as we see in Figure 4, a fixed programming impulse (top line) results in a higher response in an aged block, requiring fewer steps of the iterative programming cycle internal to the chip to reach the desired programming level. Conversely, the erase response (bottom line) lessens with repeated program/erase cycles, requiring additional internal erasure operations before reaching an adequately erased state.

#### 3.3 Performance

Read performance was tested under a number of scenarios, including random and sequential reads. Again, latency was measured from the end of the command until the chip indicated data was ready, thus avoiding effects of varying transfer speed. No significant difference was found between random and sequential speeds, nor was read performance



**Figure 6: Wear-related changes in latency.** Data points are subsampled rather than averaged to illustrate the quantized latency values due to iterative internal algorithms.



**Figure 7: Read latency by device.** Measured values were unaffected by access pattern or block wear. Virtually no variation was seen in measured values for each device. Note that specified values were unavailable for the 8 Gb SLC and 16 Gb parts.

seen to vary with program/erase cycling, and so a single average is reported for each chip. Results may be seen in Figure 7, where measured speeds are compared to speeds specified by the manufacturer.

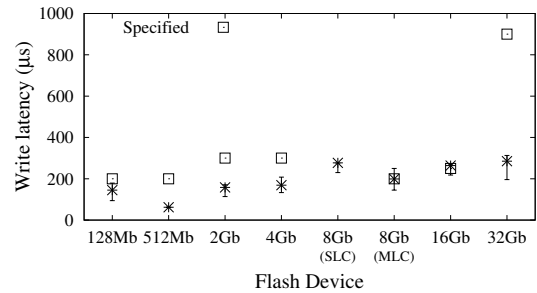
Specified read latency is typically  $25\mu s$  for current-generation SLC chips and  $50\mu s$  for MLC ones, although early small-page SLC devices are rated at  $12\mu s$ . Measured speeds under test conditions are seen to be somewhat better than specification, but (except for the 32 Gb part) not by much.

As described above, write and erase performance vary over the lifetime of a flash block, complicating the task of summarizing our measurements. The best write performance is obtained just before a block fails; however we hope to rarely if ever operate in this region. The slowest write performance occurs on fresh pages, but may speed up significantly after the first few hundred writes, leading to a sizable difference between expected and worst-case performance.

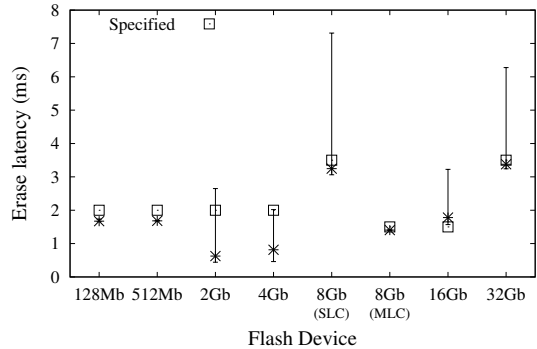
To address this we report three values for both write and erase: the worst-case latency, seen by the first writes and last erases, mean latency for the first 10000 operations on a block, and the best-case latency as seen by the first erases and last writes. Results are shown in Figures 8 and 9, again compared to manufacturer specifications when available.<sup>1</sup>

Experiments were performed to examine the effect of non-sequential writes on performance. We note that true random writes are not possible on most flash devices, as the pages

<sup>1</sup>Some test runs for the 4 Gbit device showed anomalously long write and erase delays; these runs are excluded, and we are investigating their cause.



**Figure 8: Write latency by device.** Values shown are: typical (mean of first  $10^4$  writes to a block), worst-case (mean of first 100 writes), and best-case (mean of last 100 writes before failure).



**Figure 9: Erase latency by device.** Values: typical (mean of first  $10^4$  erasures), best-case (first 100) and worst-case (last 100).

within an erase block must be written sequentially to prevent program disturbs. In effect the device is treated as a set of sequential streams, one for each erase block—writing may skip between these streams at random, but must preserve strict ordering within each stream. We therefore tested non-sequential writes across different erase blocks; no detectable difference in write performance was seen.

### 3.4 Additional Testing

Further investigation was performed to determine whether the surprisingly high endurance of the devices tested is typical, or is instead due to anomalies in the testing process. In particular, we varied both program/erase behavior and environmental conditions to determine their effects. Due to the high variance of the measured endurance values, we have not collected enough data to draw strong inferences, and so report general trends instead of detailed results.

**Usage patterns:** The results reported above were measured by repeatedly programming the first page of a block with all zeroes and then immediately erasing the entire block. Several devices were tested by writing to all pages in a block before erasing it; endurance appeared to decrease with this pattern, but by no more than a factor of two. Additional tests were performed with varying data patterns, but no difference in endurance was detected.

This result is not unexpected, as we surmise that one way in which erasure or programming fails is when a single cell fails to reach its target state after a certain number of internal program or erase steps. Given some amount of variation between cells, it is not unexpected that changing the state of a larger number of cells would result in a higher chance of failure as cells wear. (We note, however, that repeated erase cycles with no intervening writes show the same latency in-

crease and similar endurance as erasures with a single intervening page write.)

**Environmental conditions:** The processes which result in flash failure are exacerbated by heat [14], although internal temperature compensation is used to mitigate this effect [4]. The 16 Gbit device was tested at 80° C, and no noticeable difference in endurance was seen. However, at 5° C endurance was seen to drop by a factor of about two. Although not expected, this decrease of endurance at low temperature has also been reported for NOR flash [12].

We note that one of the primary differences between our tests and typical system usage is that cells are erased almost immediately after being programmed. We are curious as to whether endurance would be affected by the passage of time between program and erase or vice versa; however, the long durations required for such tests have precluded their implementation to date.

## 4. CONCLUSIONS

Many of the results of these tests were expected: read, program (with one exception) and erase times were for the most part slightly lower than the “typical” values specified by the manufacturers, perhaps reflecting a margin to account for variations outside of our test conditions.

The high endurance values measured—often nearly 100 times higher than specified—were highly unexpected and deserve more study. Further investigation is needed to determine whether such high endurance may be expected under typical system conditions, and whether any special care must be taken to achieve such behavior. If real systems can achieve average endurance levels of  $10^6$  or  $10^7$  write/erase cycles, then it would appear that many concerns raised in the systems community have been misplaced, and flash endurance may merely become another MTBF parameter, like mechanical failure in disk drives.

The variation in program and erase performance with wear, although obvious in hindsight, was also unexpected. This has obvious applications in wear leveling algorithms, as it supplies a measure of a block’s remaining lifetime that imposes no additional writes to the chip. However, it also has implications for block management on flash devices; if the latency of erasures can be hidden, then repeatedly re-using blocks until they fail may yield improved write performance. However, if system performance is impacted by erase latency, wear should be distributed as evenly as possible in order to avoid high end-of-life erase latencies.

Additional experimentation is needed to explore the endurance behavior seen in these experiments. How sensitive are these results to environmental and circuit conditions? Do they hold up across a much wider sampling of devices? And perhaps most importantly, how sensitive are they to system behavior—i.e. usage patterns and wear leveling? Work to date has focused on generating usage patterns which avoid exceeding a fixed endurance threshold for any individual block; however, it appears that this endurance level may be variable, and that it may be more profitable to look for patterns which maximize that endurance, instead.

Our results to date raise more questions than they answer, and we believe that further answers will require closer collaboration between the circuit and device community and the systems community than may have been present to date. Historically the device community has focused on worst-case behavior, as is appropriate for e.g. memory buses. However,

as systems designers we often are concerned with average-case behavior instead. We believe a deeper understanding on both sides, and focused experimentation, will help design higher-performance flash-based systems in the future.

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